2SD1539A

Silicon NPN epitaxial planar type

For low-voltage switching Complementary to 2SB1071A

■ Features

- ullet Low collector-emitter saturation voltage $V_{CE(sat)}$
- High-speed switching
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter		Symbol	Rating	Unit	
Collector-base voltage (Emitter open)		V_{CBO}	50	У	
Collector-emitter voltage (Base open)		V _{CEO}	40	V	
Emitter-base voltage (Collector open)		V_{EBO}	5	V	
Collector current		I_{C}	4	A	
Peak collector current		I_{CP}	8	A	
Collector power		P _C	25	W	
dissipation	$\Gamma_a = 25^{\circ} \text{C}$		2.0		
Junction temperature		T_j	150	°C	
Storage temperature		$T_{\rm stg}$	-55 to +150	°C	
		*			

Unit: mm 3: Emitter EIAJ: SC-67 TO-220F-A1 Package

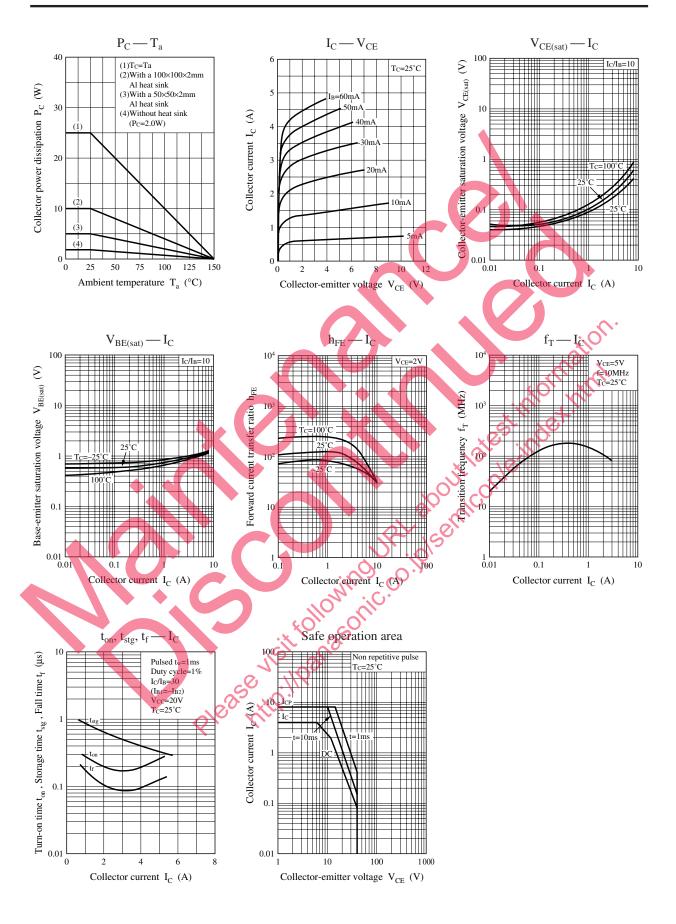
■ Electrical Characteristics $T_C = 25^{\circ}C$

Collector current	^{1}C	4		 			AL CO CZ
Peak collector current	I _{CP}	8 A		<u></u>	T T	0-220F-A	AJ: SC-67 1 Package
Collector power	P _C	25 V	V	S	76	,	
dissipation $T_a = 25^{\circ}C$		2.0		W.	1100		
Junction temperature	T_j	150		(10,10			
Storage temperature	T _{stg} -	-55 to +150 °C		, 20///			
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Parameter	Symbol	Co	onditions Q	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 10 \text{ mA}$	₹9 °O.,	40			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 50 \text{ V}, I_{E} =$	<u></u> =00°			50	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 5 \text{ V}, I_C =$	0			50	μΑ
Forward current transfer ratio	h _{FE1}	$V_{CE} = 2 V$, $I_C =$	0.1 A	45			_
	h _{FE2} *	$V_{CE} = 2 V, I_C =$	1 A	60		260	
Collector-emitter saturation voltage	VE(sat)	$I_C = 2 \text{ A}, I_B = 0.$	1 A			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_{\rm C} = 2 \text{ A}, I_{\rm B} = 0.$	1 A			1.5	V
Transition frequency	f	$V_{CE} = 5 \text{ V}, I_{C} =$	0.5 A, f = 10 MHz		120		MHz
Turn-on time	t _{on}	$I_C = 2 A, I_{B1} = 0.2 A, I_{B2} = -0.2 A$			0.2		μs
Storage time	t _{stg}	$V_{CC} = 20 \text{ V}$			0.5		μs
Fall time	t _f				0.1		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	R	Q	Р
h_{FE2}	60 to 120	90 to 180	130 to 260





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